

IN THE CLAIMS

Please amend claims 2, 3, and 6 and add claims 10 and 11 as follows:

2. (Amended) The method of claim 1 further comprising removing a dielectric layer from said upper surface prior to forming said amorphous region.

B' 3. (Amended) The method of claim 1 wherein said forming said amorphous region further comprises:

exposing a chlorine containing gas to UV radiation to form excited chlorine species;

heating said upper surface to a temperature between 50°C and 250°C; and

exposing said heated upper surface to said excited chlorine species.

B² SUB C2 6. (Amended) The method of claim 1 further comprising removing a dielectric layer from said upper surface prior to forming said amorphous region.

10. A method for forming a smooth interface between a silicon surface and a dielectric layer comprising:

providing a silicon substrate with an upper surface;

exposing a chlorine containing gas to UV radiation to form excited chlorine species;

heating said upper surface to a temperature between 50°C and 250°C;

exposing said heated upper surface to said excited chlorine species thereby forming an amorphous region on said upper surface; and

forming a dielectric layer on said amorphous region.

11. The method of claim 10 wherein said dielectric layer is formed using a material selected from the group consisting of silicon oxide, silicon nitride, silicon oxynitride, and a silicate.
